

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

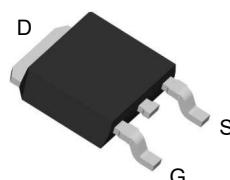
## Product Summary



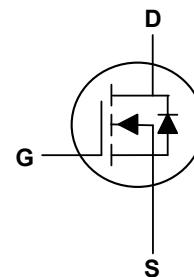
$V_{DS}$	40	V
$I_D$	150	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	2.2	mΩ

## Applications

- High Frequency Point-of-Load,Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switching



TO-252 Top View



## Absolute Maximum Ratings( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_c = 25^\circ C$	150	A
Continuous Drain Current	$I_D @ T_c = 100^\circ C$	106	A
Pulsed Drain Current	$I_{DM}$	400	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	720	mJ
Total Power Dissipation	$P_D @ T_c = 25^\circ C$	210	W
Derating factor		1.4	W/ $^\circ C$
Storage Temperature Range	$T_{STG}$	-55 to 175	$^\circ C$
Operating Junction Temperature Range	$T_J$	-55 to 175	$^\circ C$

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	0.71	$^\circ C/W$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	40	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=75\text{A}$	---	1.8	2.2	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=250\mu\text{A}$	2.0	2.7	3.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=40\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=5\text{V}$ , $I_D=75\text{A}$	---	80	---	S
Total Gate Charge	$Q_g$	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=75\text{A}$	---	81	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	13	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	10	---	
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=20\text{V}$ , $I_D=75\text{A}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=1.6\Omega$	---	12	---	ns
Rise Time	$T_r$		---	6.5	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	49	---	
Fall Time	$T_f$		---	8	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=20\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	4900	---	pF
Output Capacitance	$C_{\text{oss}}$		---	1250	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	80	---	

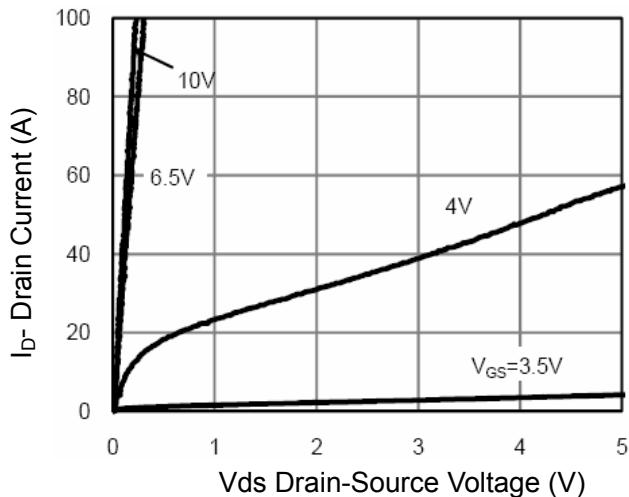
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1</sup>	$I_s$		---	---	150	A
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=75\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F=75\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	---	29	nS
Reverse Recovery Charge	$Q_{\text{rr}}$		---	---	105	nC

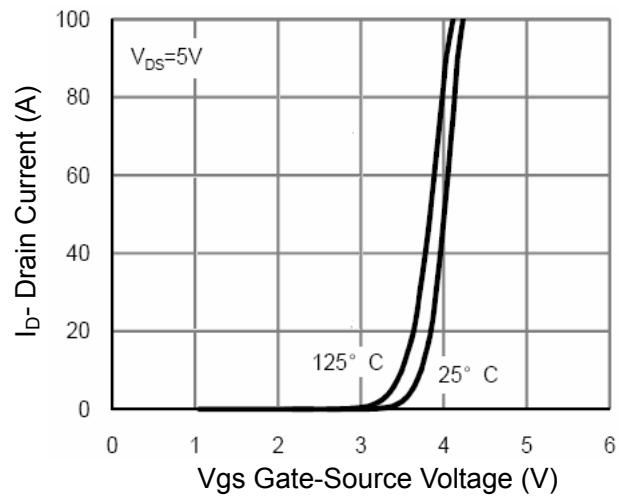
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=20\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $L=0.5\text{mH}$ , $R_G=25\Omega$

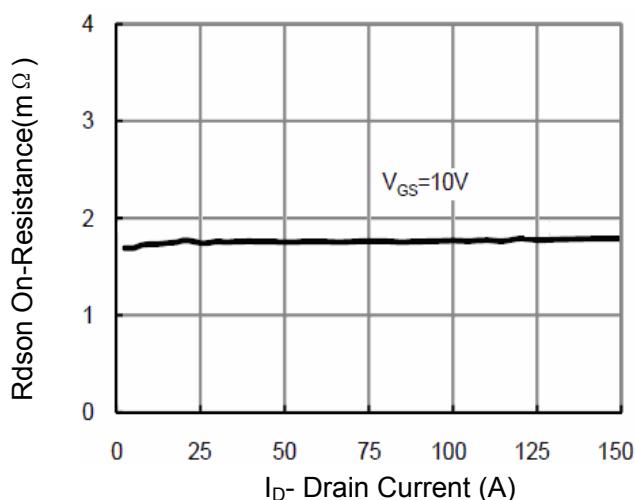
## Typical Characteristics



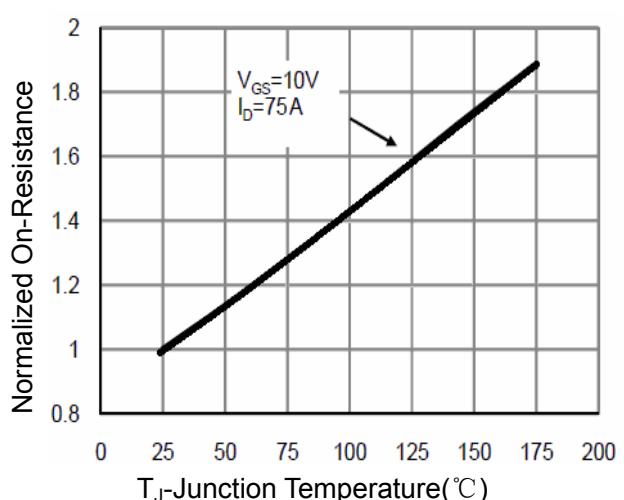
**Figure 1 Output Characteristics**



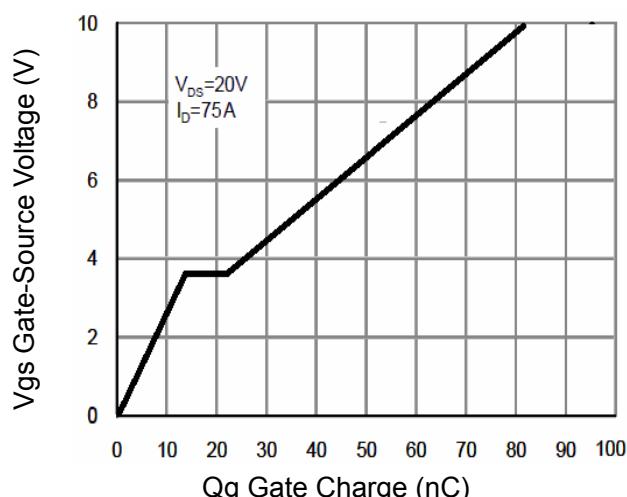
**Figure 2 Transfer Characteristics**



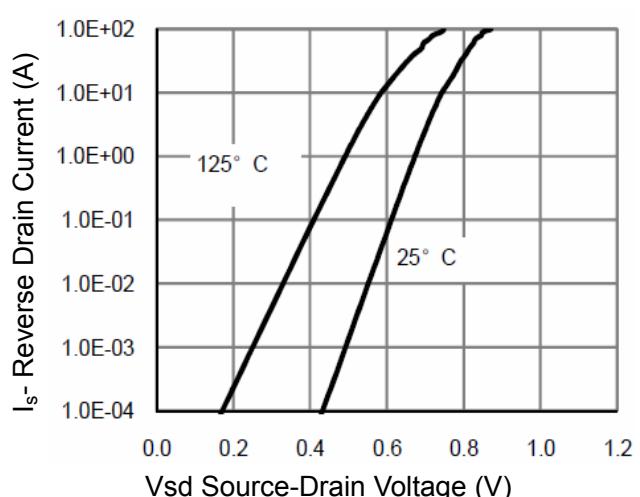
**Figure 3 Rdson- Drain Current**



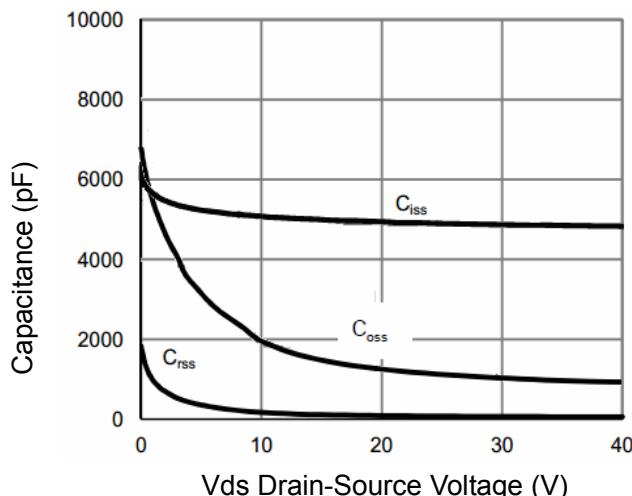
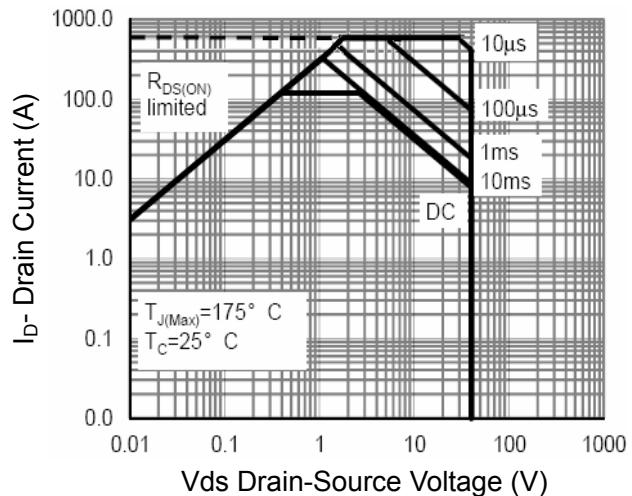
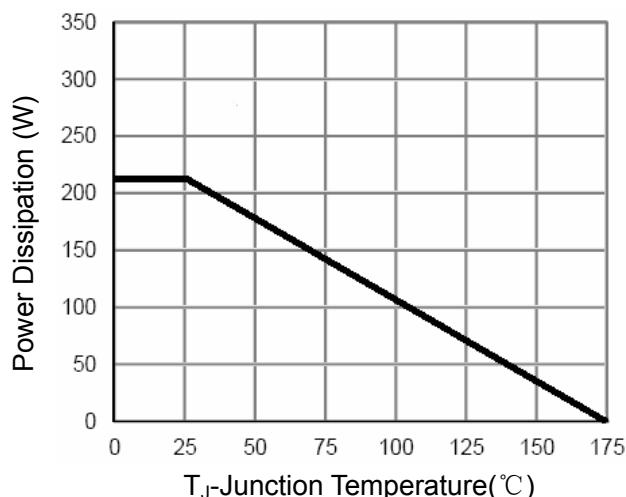
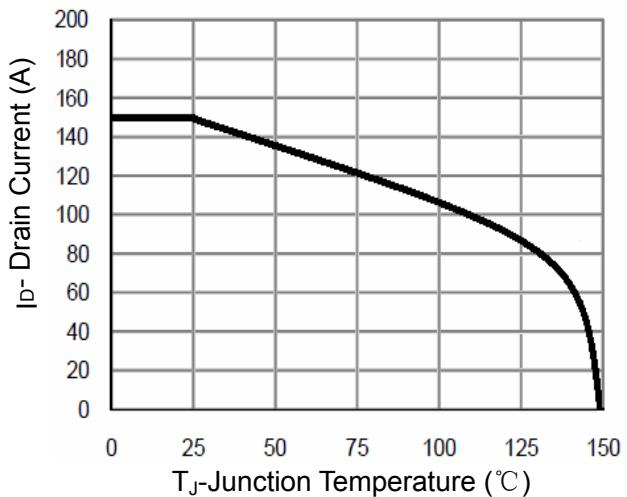
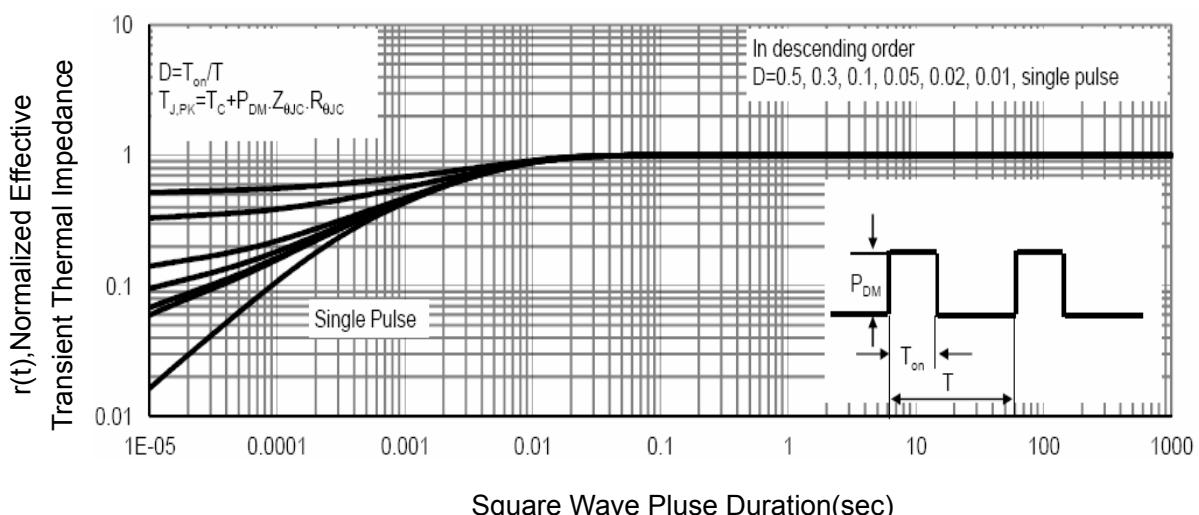
**Figure 4 Rdson-JunctionTemperature**



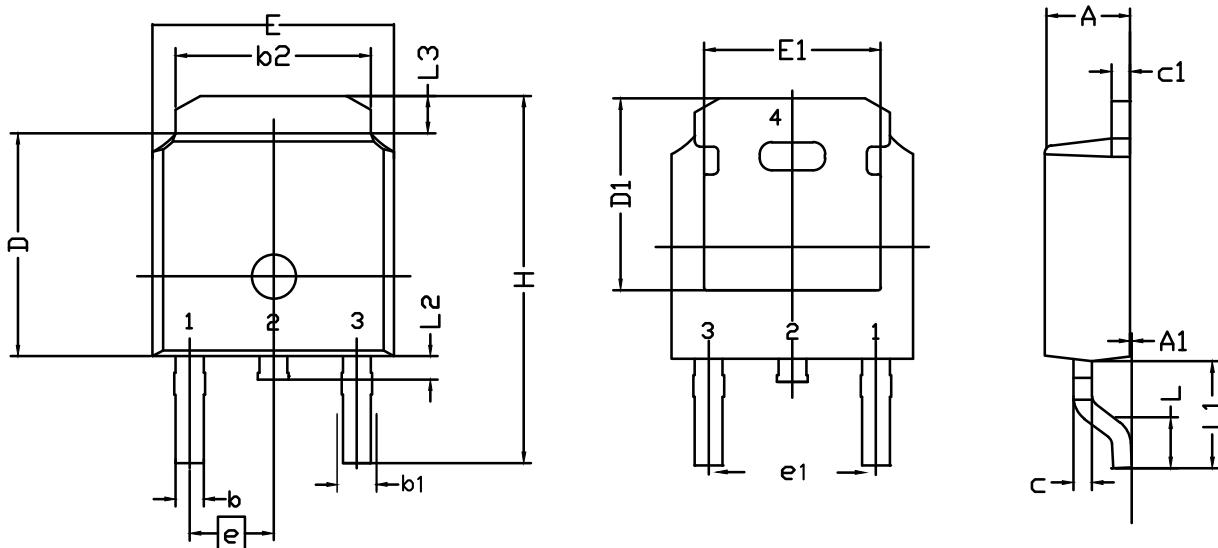
**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**


**Figure 7 Capacitance vs Vds**

**Figure 8 Safe Operation Area**

**Figure 9 Power De-rating**

**Figure 10 Current De-rating**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

### TO-252 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	2.20	2.30	2.38	<b>E</b>	6.40	6.60	6.731
<b>A<sub>1</sub></b>	0.00	0.10	0.20	<b>E<sub>1</sub></b>	4.40	--	--
<b>b</b>	0.64	0.76	0.89	<b>e</b>	2.286 BSC		
<b>b<sub>1</sub></b>	0.77	0.85	1.14	<b>e<sub>1</sub></b>	4.572 BSC		
<b>b<sub>2</sub></b>	5.00	5.33	5.46	<b>H</b>	9.40	10.00	10.40
<b>c</b>	0.458	0.508	0.610	<b>L</b>	1.40	1.52	1.77
<b>C<sub>1</sub></b>	0.458	0.508	0.620	<b>L<sub>1</sub></b>	--	2.743	--
<b>D</b>	5.98	6.10	6.223	<b>L<sub>2</sub></b>	0.60	0.80	1.01
<b>D<sub>1</sub></b>	5.20	5.25	5.38	<b>L<sub>3</sub></b>	0.90	1.06	1.25